

ABSTRACT OF THE DISCLOSURE

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DRAFT*

A semiconductor device includes an insulating film. On this insulating film, formed are an interconnection trench communicating with a semiconductor element and a pad trench communicating with the interconnection trench. In the pad trench, a 5 protrusion is formed by leaving one part of the insulating film. A conductive film is formed over the insulating film including the interconnection and pad trenches. Thereafter, the conductive film is removed by a CMP process. At this time, the protrusion serves to prevent the conductive film in the pad trench from being over-polished.